

<b>Notice of References Cited</b>	Application/Control No. 10/527,202		Applicant(s)/Patent Under Reexamination ITANO ET AL.	
	Examiner TabassomT Tadayyon-Eslami		Art Unit 1709	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,200,891	03-2001	Jagannathan et al.	438/622
*	B	US-5,120,605	06-1992	Zuel et al.	428/410
*	C	US-2003/0160026	08-2003	Klein et al.	216/83
*	D	US-6,254,796	07-2001	Rath et al.	216/87
*	E	US-3,438,799	04-1969	EMMERICHS GERHARD THEODOR; et. al.	427/327
*	F	US-4,124,516	11-1978	Shinozaki et al.	252/79.2
*	G	US-4,469,525	09-1984	Dodge, Paul D.	252/79.4
*	H	US-6,730,644	05-2004	Ishikawa et al.	510/175
*	I	US-2004/0106531	06-2004	Kanno et al.	510/175
*	J	US-2003/0235985	12-2003	Christenson et al.	438/689
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	M. A. Quevedo-Lopez et. al. , " Wet chemical etching studies of Zr and Hf-silicate gate dielectrics", Journal of Vacuum Science and Technology A, Vol 20(2002)1891.
*	V	P. S. Lysaght, et. al., " Experimental Observation of the Thermal Stability of High-K gate Dielectric Materials on Silicon", Journal of Non-Crystalline Solids, 303(2002)54.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.